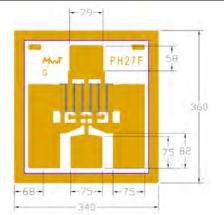




MwT-PH27F 26 GHz Medium Power AlGaAs/InGaAs pHEMT

Features:

- 25 dBm of Power at 18 GHz
- 14 dB Small Signal Gain at 18 GHz
- 45% PAE at 18 GHz
- 0.25 x 400 Micron Refractory Metal/Gold Gate
- Excellent for Medium Power, Gain, and High Power Added Efficiency
- Ideal for Commercial, Military, Hi-Rel Space Applications



Chip Dimensions: 340 x 360 microns Chip Thickness: 100 microns

Description:

The MwT-PH27F is a AlGaAs/InGaAs pHEMT (Pseudomorphic-High-Electron-Mobility-Transistor) device whose nominal 0.25 micron gate length and 400 micron gate width make it ideally suited for applications requiring high-gain and medium power up to 26 GHz frequency range. The device is equally effective for either wideband (e.g. 6 to 18 GHz) or narrow-band applications. The chip is produced using reliable metal systems and passivated to insure excellent reliability.

Electrical Specifications: at Ta= 25 °C

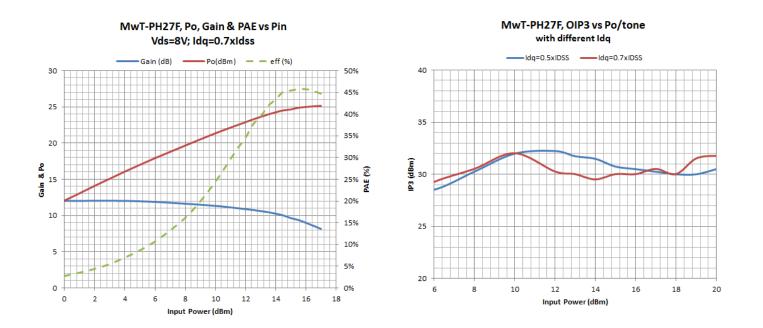
PARAMETERS & CONDITIONS	SYMBOL	FREQ	UNITS	MIN	TYP
Output Power at 1dB Compression Vds=9.0V lds=0.7xIDSS	P1dB	18 GHz	dBm		22.5
Saturated Power Vds=9.0V lds=0.7xlDSS	Psat	18 GHz	dBm		25.0
Output Third Order Intercept Point Vds=9.0V Ids=0.7xIDSS	OIP3	18 GHz	dBm		31.0
Small Signal Gain Vds=9.0V lds=0.7xlDSS	SSG	18 GHz	dB		16.0
Power Added Efficiency at P1dB Vds=9.0V lds=0.7xIDSS	PAE	18 GHz	%		45

Note: Ids should be between 40% and 80% of Idss. Currently, our data shows Ids at 70% of IDSS. Low Ids will improve efficiency, but high Ids will make Psat and IP3 better.

DC Specifications: at Ta= 25 °C

PARAMETERS & CONDITIONS		SYMBOL	UNITS	MIN	TYP	MAX
Saturated Drain Current Vds= 3.0 V Vgs= 0.0 V		IDSS	mA	90		120
Transconductance Vds= 2.5 V Vgs= 0.0 V		Gm	mS		140	
Pinch-off Voltage Vds= 3.0 V lds= 1.0 mA		Vp	V		-0.8	-1.0
Gate-to-Source Breakdown Voltage lgs= -0.3 mA		BVGSO	V		-18.0	
Gate-to-Drain Breakdown Vo lgd= -0.3 mA	bltage	BVGDO	V		-18.0	
Chip Thermal Resistance	Chip & 71 pkg 70 & 73 pkg	Rth	C/W		95 225*	

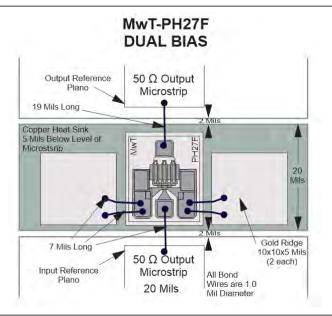
* Overall Rth depends on case mounting

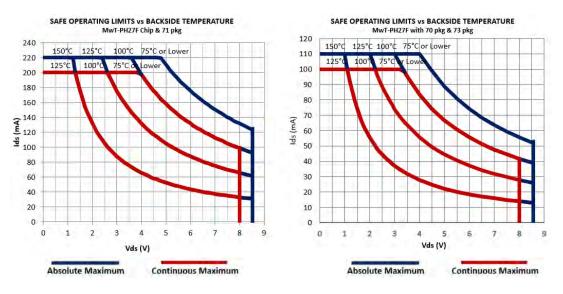


MwT-PH27F, Load Pull Data, Vdq=8V; Idq=0.7xIdss

Freq	Zs		ZL		Psat	
(GHz)	Mag	phase	mag	phase	dBm	
2	0.84	50.00	0.16	22.56	25.8	
4	0.77	90.00	0.17	33.56	25.9	
6	0.76	112.00	0.19	46.65	25.8	
8	0.79	129.00	0.28	65.03	25.6	
10	0.80	137.00	0.28	70.74	25.7	
12	0.82	149.00	0.35	78.36	25.5	
14	0.86	151.00	0.38	83.73	25.3	
16	0.83	160.00	0.38	84.90	25.3	
18	0.85	164.00	0.43	97.06	25.3	

The load pull data is based on nonlinear model provided by the foundry that processes the device.





Symbol Parameter Units Cont Max1 Absolute Max2 VDS Drain to Source Volt. ٧ 8.0 8.5 °C **Channel Temperature** +150 +175 Tch °C +175 Tst Storage Temperature -65 to +150 Pin **RF Input Power** mW 130 200

Absolute Maximum Rating

Notes:

1. Exceeding any one of these limits in continuous operation may reduce the mean-time- to-failure below the design goal.

2. Exceeding any one of these limits may cause permanent damage.

S-Parameters

S-PARAMETER Vds=8V, Ids= 0.7 x Idss S11 S12 S22 К GMAX Freq. S21 GHz dB dB dB Ang (°) Ang (°) dB dB Ang (°) Ang (°) -0.231 -32.694 19.665 158.071 -36.548 72.399 -2.160 -8.934 0.115 28,106 1 2 -0.640-61.163 18.651 140.369 -31.601 59.978 -2.67215.713 0.166 25.126 -85.153 17.410 125.221 -29.335 48.992 0.241 23.373 3 -1.079 -3.170 21.042 -1.386 -104.475 16.169 112.916 -28.102 41.107 0.302 4 -3.610 24.819 22.135 -1.761 -119.922 14.784 102.685 -27.581 35.053 -4.099 0.417 5 28.464 21.182 -1.983 -131.782 13.725 94.677 -27.048 31.418 -4.315 30.382 0.491 20.387 6 7 -2.195 -143.772 12.685 86.683 -26.970 28.522 -4.557 32.770 0.594 19.827 8 -2.134 -152.508 11.837 79.877 -26.604 26.067 -37.131 0.599 19.221 -4.718 9 -161.518 10.655 72.635 -26.825 25.021 -5.079 0.732 18.740 -2.148 39.773 10 -168.517 10.045 66.584 22.641 -4.987 43.411 0.753 18.359 -2.158 -26.674 -175.835 9.363 59.695 -26.844 22.444 46.034 0.794 18.104 11 -2.025 -5.178 12 -1.978 178.553 8.602 54.635 -26.802 21.868 -5.321 49.977 0.847 17,702 13 -1.996 173.295 7.922 48.918 -26.939 22.962 -5.368 -53.571 0.936 17.430 14 -1.927 168.420 7.163 43.642 -26.876 23.745 -5.449 57.977 0.978 17.019 163.936 38.677 -26.939 1.025 15 -1.8986.736 25.503 -5.572 -61.784 15.867 16 -1.827 159.393 6.173 34.214 -26.768 28.271 -5.517 66.454 0.999 16.470 17 -1.893 155.811 5.549 29.308 -26.693 29.474 -5.498 72.013 1.104 14.159 25.013 18 -1.663 152.829 4.955 -26.406 32.946 -5.506 77.229 0.976 15.680 20.792 19 -1.645 151.205 4.537 -26.107 35.919 -5.459 81.318 0.963 15.322 15.854 -25.883 0.943 14.994 20 -1.565 145.351 4.104 36.755 -5.557 86.388 9.574 14.449 21 -1.581 143.051 3.545 -25.354 38.691 -5.335 92.138 0.919 22 -1.579 140.188 3.124 5.470 -25.001 40.464 -5.284 97.372 0.918 14.063 0.691 0.745 23 -1.402 138.352 2.664 -24.223 41.543 -5.284 -103.922 13.443 24 -1.362 135.736 2.220 -4.336 -23.845 41.498 -5.275 -110.968 0.727 13.033 25 -1.418 133.109 1.672 -8.620 -23.266 42.930 -5.038 -117.456 0.740 12.469 26 -1.321 130.648 1.212 -13.116 -22.760 44.637 -4.872 -123.799 0.653 11.986 -18.101 27 -1.187 128.092 0.790 -22.283 45.873 -4.615 -129.916 0.526 11.537 28 -1.114 127.122 0.390 -22.352 -21.403 41.984 -4.480 -136.4440.403 10.896 -0.153 -26.948 -20.886 42.084 0.418 29 -1.131 123.760 -4.328 -142.81510.367 -1.124 122.425 -0.592 -20.361 9.884 30 -31.182 40.077 -4.008 -149.395 0.363

Available Packaging:

70 Package - MwT-PH27F70 71 Package - MwT-PH27F71

73 Package - MwT-PH27F73

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